Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

H9012

■ **1W OUTPUT AMPLIFIER OF POTABLE RADIOS IN CLASS B PUSH-PULL OPERATION.**

■ ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature…… -55~150℃

T_j——Junction Temperature……150℃

P_C——Collector Dissipation……625mW

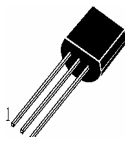
V_{CBO}——Collector-Base Voltage……-40V

V_{CEO}——Collector-Emitter Voltage……-20V

V_{EBO}——Emitter-Base Voltage……-5V

I_C——Collector Current……-500mA

TO-92



1—Emitter，E
2—Base，B
3—Collector，C

■ ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector Cut-off Current			-100	nA	V_{CB}=-25V, I_E=0
I_{EBO}	Emitter Cut-off Current			-100	nA	V_{EB}=-3V, I_C=0
$H_{FE(1)}$	DC Current Gain	78		246		V_{CE}=-1V, I_C=-50mA
$H_{FE(2)}$		40				V_{CE}=-1V, I_C=-500mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-600	mV	I_C=-500mA, I_B=-50mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage			-1.2	V	I_C=-500mA, I_B=-50mA
$V_{BE(ON)}$	Base-Emitter On Voltage	-600		-730	mV	V_{CE}=-1V, I_C=-10mA
BV_{CBO}	Collector-Base Breakdown Voltage	-40			V	I_C=-100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-20			V	I_C=-1mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	I_E=-100μA，I_C=0

■ h_{FE} Classification

E	F	G	H	I
78—112	96—135	112—166	144—202	176—246

Typical Characteristics

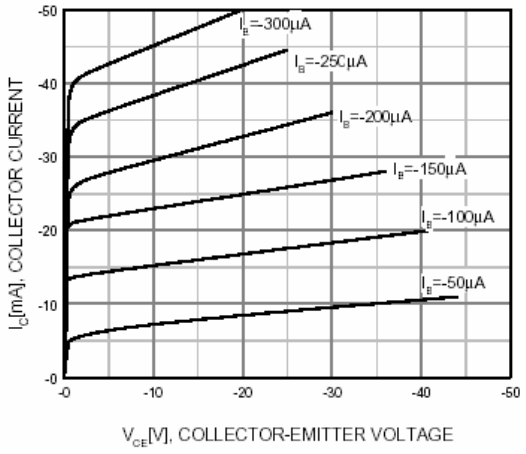


Figure 1. Static Characteristic

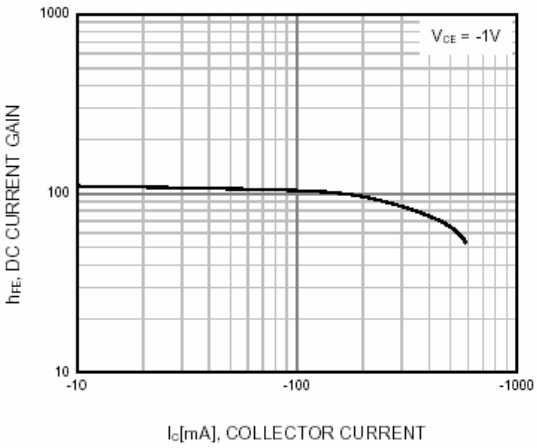


Figure 2. DC current Gain

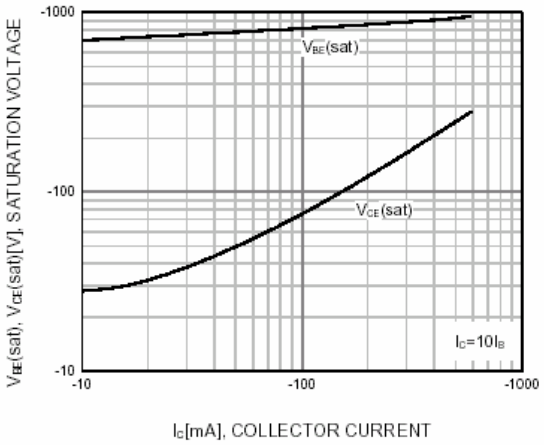


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

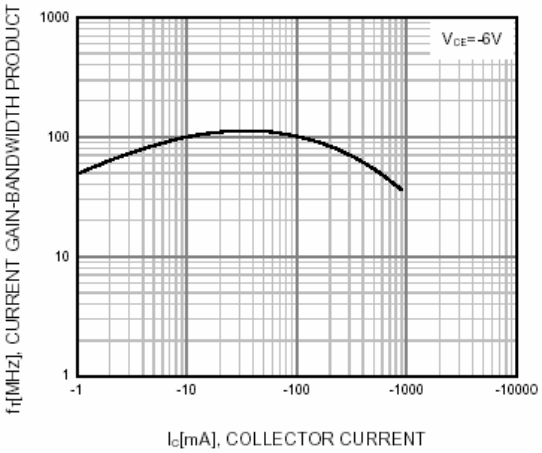


Figure 4. Current Gain Bandwidth Product